

#4 Pre-Amendment  
6-5-2001

Via Express Mail Label #EL914109965US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: NOBUHIKO ODA, ET AL.

FOR: BOTTOM GATE-TYPE THIN-FILM TRANSISTOR AND METHOD FOR  
MANUFACTURING THE SAME

**PRELIMINARY AMENDMENT**

Box Patent Application  
The Assistant Commissioner of  
Patents and Trademarks  
Washington, DC 02031

Sir:

Prior to the Examiner acting in the above-referenced application, please preliminary amend the abstract as follows:

**IN THE ABSTRACT:**

Please amend the abstract as follows:

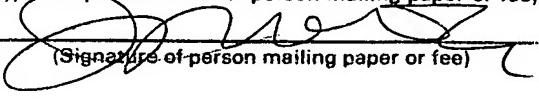
**ABSTRACT OF DISCLOSURE**

In a bottom gate-type thin-film transistor manufacturing method, after ion doping, an ion stopper is removed. The ion stopper does not remain in the interlayer insulating film lying immediately above the gate electrode. The thin-film transistor has such a structure that no ion stopper, and the interlayer insulating layer is in direct contact with at least the channel region of the semiconductor layer. The impurity concentration in the vicinity of the interface between the interlayer insulating film and the semiconductor layer 4 is  $10^{18}$  atoms/cc or less. This structure can prevent the back channel phenomenon and reduce variations in characteristic resulting from variations in manufacturing.

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Date of Deposit November 6, 2001

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Jennifer Matsan  
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